

## 1700 MHz to 2200 MHz 1 WATT POWER AMP WITH ACTIVE BIAS

RFMD Green, RoHS Compliant, Pb-Free (Z Part Number)
Package: ESOP-8



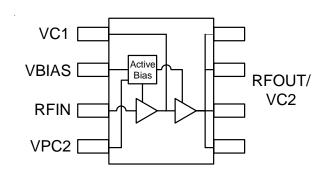
#### **Product Description**

RFMD's SPA-2318 is a high efficiency GaAs Heterojunction Bipolar Transistor (HBT) amplifier housed in a low-cost surface-mountable plastic package. These HBT amplifiers are fabricated using molecular beam epitaxial growth technology which produces reliable and consistent performance from wafer to wafer and lot to lot. This product is specifically designed for use as a driver amplifier for infrastructure equipment in the 1960MHz and 2140MHz bands. Its high linearity makes it an ideal choice for multi-carrier and digital applications. The matte tin finish on the lead-free package utilizes a post annealing process to mitigate tin whisker forma-

Optimum Technology
Matching® Applied

✓ GaAs HBT
GaAs MESFET
InGaP HBT
SiGe BiCMOS
Si BiCMOS
SiGe HBT
GaAs pHEMT
Si CMOS
Si BJT
GaN HEMT
RF MEMS

tion and is RoHS compliant per EU Directive 2002/95. This package is also manufactured with green molding compounds that contain no antimony trioxide or halogenated fire retardants.



#### **Features**

- Now Available in Lead-Free, RoHS Compliant, and Green Packaging
- High Linearity Performance:
   +21dBm IS-95 Channel
   Power at -55dBc ACP;
   +20.7dBm WCDMA Channel
   Power at -50dBc ACP;
   +47dBm Typ. OIP<sub>3</sub>
- On-Chip Active Bias Control
- High Gain: 24dB Typ. at 1960MHz
- Patented High Reliability GaAs HBT Technology
- Surface-Mountable Plastic Package

#### **Applications**

- WCDMA Systems
- PCS Systems
- Multi-Carrier Applications

Parameter	Specification			Unit	Condition
rarameter	Min.	Тур.	Max.	Unit	Condition
Frequency of Operation	1700		2200	MHz	
Output Power at 1dB Compression [1]		29.5		dBm	1960MHz
		29.5		dBm	2140MHz
Adjacent Channel Power [1]		-55.0		dBc	1960 MHz, IS-95 at P <sub>OUT</sub> =21.0 dBm, WCDMA at P <sub>OUT</sub> =20.7 dBm
		-50.0	-47.0	dBc	2140MHz
Small Signal Gain [1,2]		24.0		dB	1960MHz
	21.0	23.5	24.5	dB	2140 MHz
Input VSWR [1,2]		1.6:1			1960MHz
		1.6:1			2140MHz
Output Third Order Intercept Point [2]		46.5		dBm	1960MHz, Power out per tone=+14dBm
		47.0		dBm	2140MHz
Noise Figure <sup>[1,2]</sup>		5.5		dB	1960MHz
		5.5		dB	2140MHz
Device Current [1,2]	360	400	425	mA	I <sub>BIAS</sub> =10 mA, I <sub>C1</sub> =70 mA, I <sub>C2</sub> =320 mA
Device Voltage [1,2]	4.75	5.0	5.25	V	
Thermal Resistance (Junction - Lead)		31		°C/W	T <sub>L</sub> =85°C

Test Conditions:  $Z_0$ =50 $\Omega$  Temp=25°C  $V_{CC}$ =5.0V [1] Optimal ACP tune [2] Optimal IP<sub>3</sub> tune



#### **Absolute Maximum Ratings**

Parameter	Rating	Unit
Max Supply Current ( $I_{C1}$ ) at $V_{CC}$ typ.	150	mA
Max Supply Current ( $I_{C2}$ ) at $V_{CC}$ typ.	750	mA
Max Device Voltage (V <sub>CC</sub> ) at I <sub>CC</sub> typ.	6.0	V
Max RF Input Power	16	dBm
Max Junction Temp (T <sub>J</sub> )	+160	°C
Max Storage Temp	+150	°C

Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one.

Bias Conditions should also satisfy the following expression:

 $I_DV_D < (T_J - T_L) / R_{TH}, j-I$ 



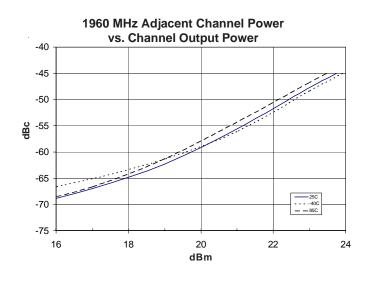
#### Caution! ESD sensitive device.

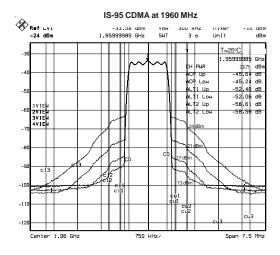
Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

RoHS status based on EUDirective 2002/95/EC (at time of this document revision).

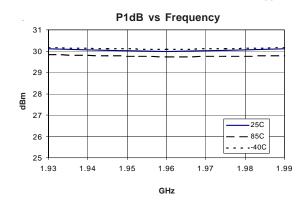
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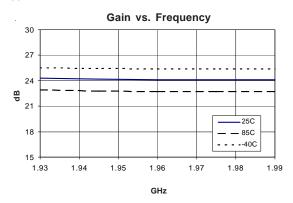
#### ACP Optimized 1960MHz Application Circuit Data, I<sub>CC</sub>=400mA, V<sub>CC</sub>=5V IS-95, 9 Channels Forward





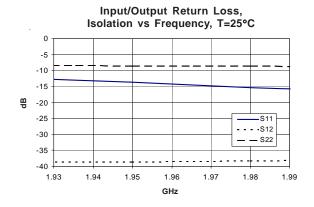
#### ACP Optimized 1960MHz Application Circuit Data, $I_{CC}$ =400mA, $V_{CC}$ =5V

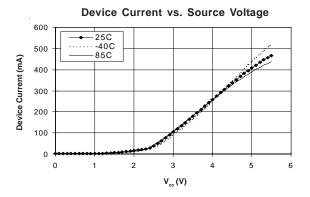




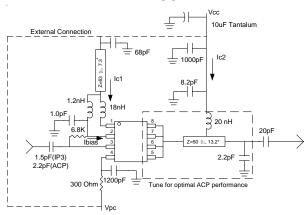


#### ACP Optimized 1960MHz Application Circuit Data, $I_{CC}$ =400mA, $V_{CC}$ =5V

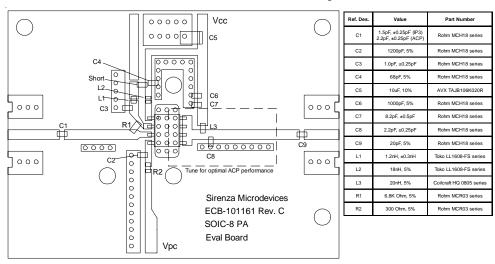




### 1930 MHz to 1990 MHz Application Schematic

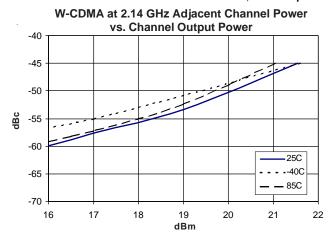


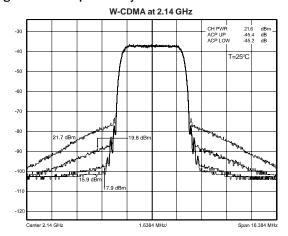
### 1930 MHz to 1990 MHz Evaluation Board Layout and Bill of Materials



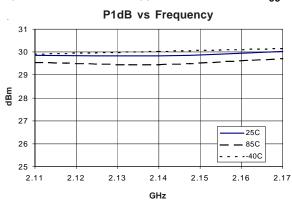


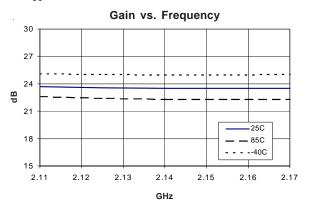
ACP Optimized 2140 MHz Application Circuit Data,  $I_{CC}$ =400 mA,  $V_{CC}$ =5V IS-95, WCDMA setup is PCCPCH+PSCH+SSCH+CPICH+PICH+64 DPCH, 10.5 dB peak to average at 0.001% probability

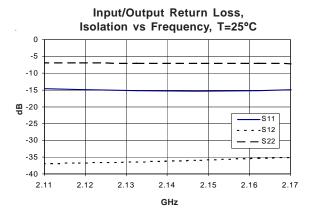


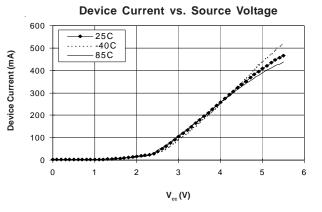


#### ACP Optimized at 2140 MHz Application Circuit Data, $I_{CC}$ = 400 mA, $V_{CC}$ = 5V



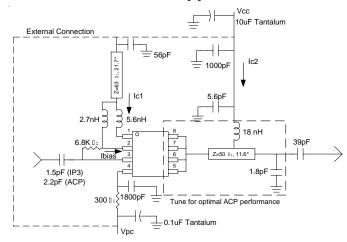




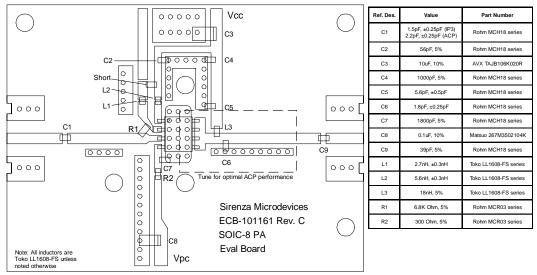




### 2110 MHz to 2170 MHz Application Schematic



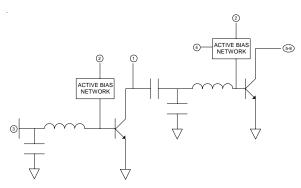
## 2110 MHz to 2170 MHz Evaluation Board Layout and Bill of Materials





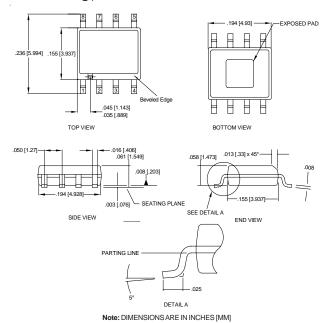
Pin	Function	Description	
1	VC1	VC1 is the supply voltage for the first stage transistor. The configuration as shown on the Application Schematic is required for optimum RF performance.	
2	VBIAS	VBias is the bias control pin for the active bias network. Recommended configuration is shown in the Application Schematic.	
3	RF IN	RF input pin. This pin requires the use of an external DC blocking capacitor as shown in the Application Schematic.	
4	VPC2	VPC2 is the bias control pin for the active bias network for the second stage. The recommended configuration is shown in the Application Schematic.	
5, 6,	RF OUT / VC2	RF output and bias pins. Bias should be supplied to this pin through an external RF choke. Because DC biasing is prese on this pin, a DC blocking capacitor should be used in most applications (see Application Schematic). The supply side	
7, 8		the bias network should be well bypassed. An output matching network is necessary for optimum performance.	
EPAD	GND	Exposed area on the bottom side of the package needs to be soldered to the ground plane of the board for thermal and RF performance. Several vias should be located under the EPAD as shown in the recommended land pattern.	

## **Simplified Device Schematic**



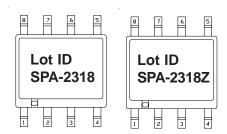
## **Package Drawing**

Dimensions in inches (millimeters)
Refer to drawing posted at www.rfmd.com for tolerances.

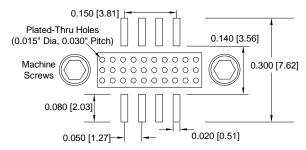




## **Part Identification Marking**



#### **Recommended Land Pattern**



## **Ordering Information**

Part Number	Reel Size	Devices/Reel
SPA-2318	7"	500
SPA-2318Z	7"	500

